

	Type	L #	Hits	Search Text	DBs
1	BRS	L2	42	"438"/\$.ccls. and (substrate board carrier) same (via hole) and plasma same (silicon adj (film layer)) same silicon adj nitride and tungsten with (via hole)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L3	53	"257"/\$.ccls. and (substrate board carrier) same (via hole) and plasma same (silicon adj (film layer)) same silicon adj nitride and tungsten with (via hole)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L4	53	"257"/\$.ccls. and (substrate board carrier) same (via hole) and plasma same (silicon adj (film layer material)) same silicon adj nitride and tungsten with (via hole)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L5	0	"29"/\$.ccls. and (substrate board carrier) same (via hole) and plasma same (silicon adj (film layer material)) same silicon adj nitride and tungsten with (via hole)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L6	0	"361"/\$.cccls. and (substrate board carrier) same (via hole) and plasma same (silicon adj (film layer material)) same silicon adj nitride and tungsten with (via hole)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B